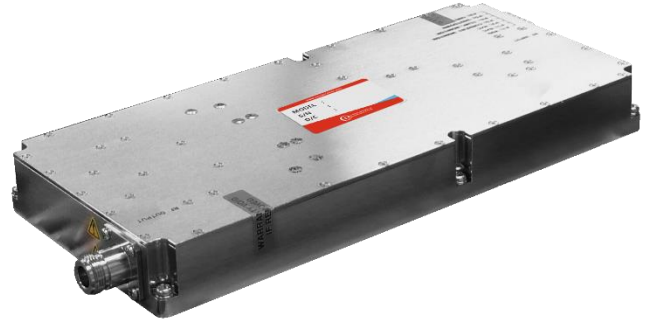


AMP1135 SOLID STATE HIGH POWER AMPLIFIER

FEATURES

- Class AB linear LDMOS design
- Instantaneous ultra-wide bandwidth
- Suitable for all single channel modulation standards
- Designed HF communications applications
- Built-in protection circuits
- High reliability and ruggedness
- Small form factor, high power density



ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	2 - 30 MHz	
Power Output Psat	1000 Watt typ	800W min CW
Power Gain	60 dB Min	
Gain Flatness	2.0 dB p-p Max	Constant input power
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	43dBm/Tone, Δ = 1MHz
Harmonics	2 nd	At rated Pout
	3 rd	
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	50 VDC Nom	
Current Consumption	43 Amp Max	At rated Pout
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout
Turn On / Off Speed	5 μSec Max	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	350 x 120 x 35 mm	Excluding connectors
Weight	4 Kg.	
RF Connectors In/Out	SMA female / Type-N female	
DC Power / Interface Connector	9-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

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D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	FWD	N/C
2	REV	N/C
3	CURRENT SENSOR	$I_D @ 20mV/100mA$ Typ
4	TEMP SENSOR	$V_T @ 10mV/^{\circ}C + 500mV$ Typ
5	SHUTDOWN	TTL
A1, A2	VDD	28VDC
A3, A4	GND	Ground

OUTLINE DRAWING

